## In the Claims

Claims 1-35 are canceled.

 $\left(\frac{1}{2}\right)$ 

36. [Amended] A semiconductor workpiece processing method comprising:

providing a semiconductor process chamber;

supplying slurry to the semiconductor process chamber; and

monitoring the turbidity of the slurry during the supplying using a sensor.

37. [Original] The method according to claim 36 wherein the supplying comprises using a supply connection and the monitoring comprises monitoring slurry within the supply connection.

5 38. [Original] The method according to claim 37 further comprising coupling the sensor with the supply connection.

A 39. [Original] The method according to claim 36 wherein the monitoring comprises:

emitting electromagnetic energy towards the slurry; and receiving at least some of the electromagnetic energy.

40. [Original] The method according to claim 36 further comprising generating a signal indicative of the turbidity after the monitoring.

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42. [Original] The method according to claim 36 wherein the providing comprises providing a chemical-mechanical polishing process chamber.

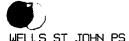
Claims 43-52 are canceled.

53. [Original] A semiconductor workpiece processing method comprising:

providing a semiconductor processor having a process chamber configured to
receive a semiconductor workpiece;

supplying slurry to the process chamber using a connection;
emitting electromagnetic energy towards the connection using a sensor;
receiving at least some of the electromagnetic energy using the sensor; and
generating a signal indicative of turbidity of the slurry responsive to the receiving.

- 54. [Original] The method according to claim 53 wherein the emitting comprises emitting infrared electromagnetic energy.
- 55. [Original] The method according to claim 53 further comprising substantially insulating the slurry from the sensor.



- [Original] The method according to claim 53 wherein the providing comprises providing chemical-mechanical polishing semiconductor processor.
- [Original] The method according to claim 53 further comprising attaching the 57. sensor to the connection and detaching the sensor from the connection while maintaining the supplying.
- [Original] A semiconductor workpiece processing method comprising: **58**. providing a semiconductor processor having a process chamber configured to receive a semiconductor workpiece;

supplying slurry to the process chamber using a connection; emitting infrared electromagnetic energy using a source;

splitting the infrared electromagnetic energy to direct some of the infrared electromagnetic energy towards the connection;

first receiving at least some of the infrared electromagnetic energy passing through the connection using a first receiver,

generating a feedback signal using the first receiver responsive to the first receiving; adjusting the emitting via the source responsive to the feedback signal to provide a substantially constant amount of electromagnetic energy to the first receiver;

second receiving at least some of the infrared electromagnetic energy not passing through the connection using a second receiver; and

generating a signal indicative of turbidity of the slurry using the second receiver responsive to the second receiving.

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59. [New] The method according to claim 36 further comprising providing the slurry and the monitoring comprises monitoring after the providing.

60. [New] The method according to claim 37 wherein the supply connection is configured to supply the slurry in at least a partially horizontal direction.